

Description

The 9FGV1001 is a member of IDT's PhiClock™ programmable clock generator family. The 9FGV1001 provides four non-spread spectrum copies of a single output frequency and two copies of the crystal reference input. Two select pins allow for hardware selection of the desired configuration, or two I²C bits allow easy software selection of the desired configuration. The user may configure any one of the four OTP configurations as the default when operating in I²C mode. Four unique I²C addresses are available, allowing easy I²C access to multiple components.

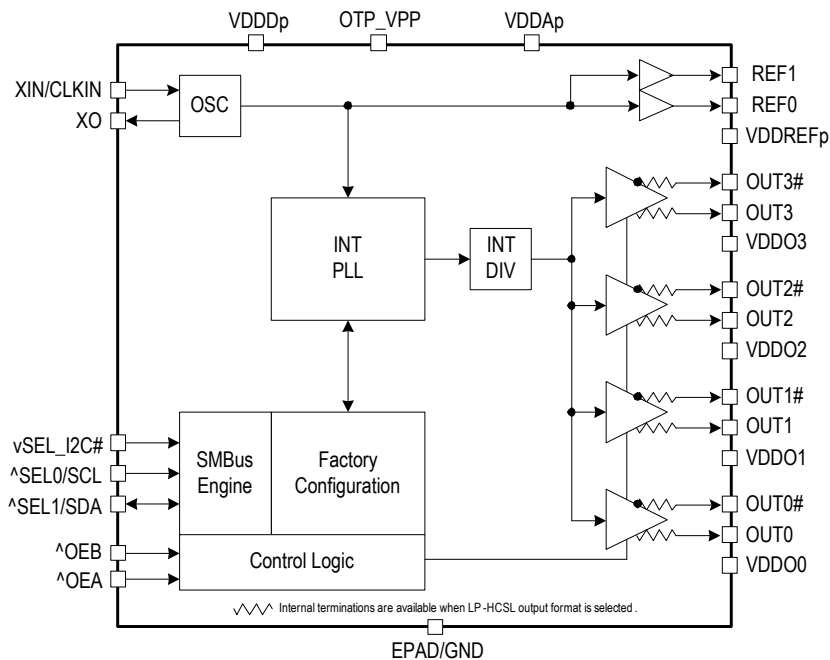
Typical Applications

- HPC
- Storage
- 10G/25G Ethernet
- Fiber Optic Modules
- SSDs

Output Features

- 4 programmable output pairs plus 2 LVCMOS REF outputs
- 1 integer output frequency per configuration
- 10MHz–325MHz output frequency (LVDS or LP-HCSL output configuration)
- 10MHz–200MHz output frequency (LVCMOS output configuration)

Block Diagram



Features

- 1.8V–3.3V core V_{DD} and V_{DDREF}
- Individual 1.8V–3.3V V_{DDO} for each programmable output pair
- Supports HCSL, LVDS and LVCMOS I/O standards
- Supports LVPECL and CML logic with easy AC coupling – see application note [AN-891](#) for alternate terminations
- HCSL utilizes IDT's LP-HCSL technology for improved performance, lower power and higher integration:
 - Programmable output impedance of 85 or 100 Ω
- On-board OTP supports up to 4 complete configurations
- Configuration selected via strapping pins or I²C
- < 125mW at 1.8V, < 230mW at 3.3V with outputs running at 100MHz
- 4 programmable I²C addresses: D0/D1, D2/D3, D4/D5, D6/D7 read/write
- Supported by IDT [Timing Commander™](#) software
- 4 × 4 mm 24-VFQFPN; minimal board space

Key Specifications

- 259fs rms typical phase jitter outputs at 156.25MHz (12kHz–20MHz)
- PCIe Gen1–4 compliant

PCIe Clocking Architectures Supported

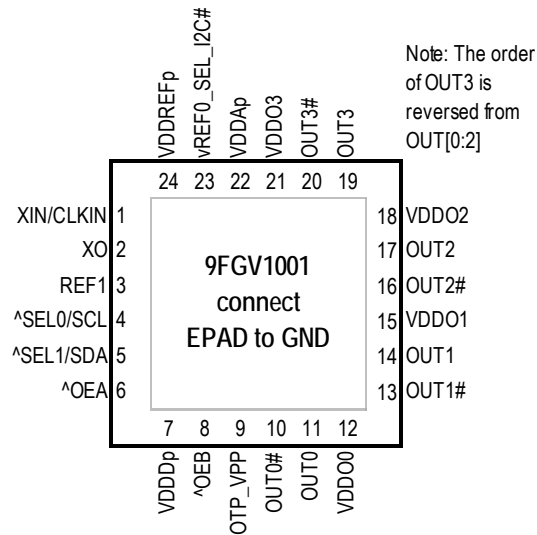
- Common Clocked (CC)
- Independent Reference without spread spectrum (SRnS)

Table 1. OE Mapping

| OE[B:A] | OUT0 | OUT1 | OUT2 | OUT3 | REF0 | REF1 |
|---------|---------|---------|---------|---------|---------|---------|
| 00 | Running | Stopped | Stopped | Stopped | Running | Running |
| 01 | Running | Running | Stopped | Stopped | Running | Running |
| 10 | Running | Running | Running | Stopped | Running | Running |
| 11 | Running | Running | Running | Running | Running | Running |

Pin Assignments

Figure 1. Pin Assignments for 4 x 4 mm 24-VFQFPN Package – Top View



4 × 4 mm 24-VFQFPN, 0.5mm pitch

^ prefix indicates internal 120kOhm pull-up resistor
 v prefix indicates internal 120kOhm pull-down resistor

Pin Descriptions

Table 2. Pin Descriptions

| Number | Name | Type | Description |
|--------|-----------|--------|---|
| 1 | XIN/CLKIN | Input | Crystal input or reference clock input. |
| 2 | XO | Output | Crystal output. |
| 3 | REF1 | Output | LVC MOS reference output. |
| 4 | ^SEL0/SCL | Input | Select pin for internal frequency configurations/I ² C clock pin. Function is determined by state of SEL_I2C# upon power-up. This pin has an internal pull-up. |
| 5 | ^SEL1/SDA | I/O | Select pin for internal frequency configurations/I ² C data pin. Function is determined by state of SEL_I2C# upon power-up. This pin has an internal pull-up. |
| 6 | ^OEa | Input | Active high input for enabling outputs. This pin has an internal pull-up resistor. 0 = disable outputs, 1 = enable outputs. |

Table 2. Pin Descriptions (Cont.)

| Number | Name | Type | Description |
|--------|---------------------|-------------|--|
| 7 | V _{DDDP} | Power | Digital power. 1.8V to 3.3V. V _{DDAp} and V _{DDDP} should be connected to the same power supply. |
| 8 | ^OE _B | Input | Active high input for enabling outputs. This pin has an internal pull-up resistor. 0 = disable outputs, 1 = enable outputs. |
| 9 | OTP_VPP | Power | Voltage for programming OTP. During normal operation, this pin should be connected to the same power rail as V _{DDD} . |
| 10 | OUT0# | Output | Complementary output clock 0. |
| 11 | OUT0 | Output | Output clock 0. |
| 12 | V _{DDO0} | Power | Power supply for output 0. |
| 13 | OUT1# | Output | Complementary output clock 1. |
| 14 | OUT1 | Output | Output clock 1. |
| 15 | V _{DDO1} | Power | Power supply for output 1. |
| 16 | OUT2# | Output | Complementary output clock 2. |
| 17 | OUT2 | Output | Output clock 2. |
| 18 | V _{DDO2} | Power | Power supply for output 2. |
| 19 | OUT3 | Output | Output clock 3. |
| 20 | OUT3# | Output | Complementary output clock 3. |
| 21 | V _{DDO3} | Power | Power supply for output 3. |
| 22 | V _{DDAp} | Power | Power supply for analog circuits. V _{DDAp} and V _{DDDP} should be connected to the same power supply. Programmable for nominal voltages of 1.8V, 2.5V or 3.3V. |
| 23 | vREF0_SEL_I2C# | Latched I/O | Latched input/LVCMOS output. At power-up, the state of this pin is latched to select the state of the I ² C pins. After power-up, the pin acts as an LVCMOS reference output. This pin has an internal pull-down. 1 = SEL0/SEL1. 0 = SCL/SDA. |
| 24 | V _{DDREFp} | Power | Power supply for REF0 and REF1 and the internal XO. Programmable to 1.8V, 2.5V or 3.3V. |
| 25 | EPAD | GND | Connect to ground. |

Note: Unused outputs can be programmed off and left floating. V_{DDREF} and V_{DDO0} have to be connected.

Absolute Maximum Ratings

The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the 9FGV1001 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 3. Absolute Maximum Ratings

| Parameter | Rating |
|---|---------------------------|
| Supply Voltage, V_{DDA} , V_{DDD} , V_{DDO} | 3.465V |
| Storage Temperature, T_{STG} | -65°C to 150°C |
| ESD Human Body Model | 2000V |
| Junction Temperature | 125°C |
| Inputs | |
| XIN/CLKIN | 0V to 1.2V voltage swing |
| Other Inputs | -0.5V to V_{DDD} |
| Outputs | |
| Outputs, V_{DDO} (LVCMOS) | -0.5V to $V_{DDO} + 0.5V$ |
| Outputs, IO (SDA) | 10mA |

Thermal Characteristics

Table 4. Thermal Characteristics

| Parameter | Symbol | Conditions | Package | Typical Values | Units | Notes |
|---|----------------|----------------------------------|---------|----------------|-------|-------|
| Thermal Resistance (devices with external crystal) | θ_{JC} | Junction to case. | NBG24 | 52 | °C/W | 1 |
| | θ_{Jb} | Junction to base. | | 2.3 | °C/W | 1 |
| | θ_{JA0} | Junction to air, still air. | | 44 | °C/W | 1 |
| | θ_{JA1} | Junction to air, 1 m/s air flow. | | 37 | °C/W | 1 |
| | θ_{JA3} | Junction to air, 3 m/s air flow. | | 33 | °C/W | 1 |
| | θ_{JA5} | Junction to air, 5 m/s air flow. | | 32 | °C/W | 1 |

¹ EPAD soldered to board.

Recommended Operating Conditions

Table 5. Recommended Operating Conditions

| Symbol | Parameter | Minimum | Typical | Maximum | Units |
|------------|---|---------|---------|---------|-------|
| V_{DDOX} | Power supply voltage for supporting 1.8V outputs. | 1.71 | 1.8 | 1.89 | V |
| | Power supply voltage for supporting 2.5V outputs. | 2.375 | 2.5 | 2.625 | V |
| | Power supply voltage for supporting 3.3V outputs. | 3.135 | 3.3 | 3.465 | V |
| V_{DDD} | Power supply voltage for core logic functions. | 1.71 | | 3.465 | V |
| V_{DDA} | Analog power supply voltage. Use filtered analog power supply if available. | 1.71 | | 3.465 | V |
| T_A | Operating temperature, ambient. | -40 | | 85 | °C |
| C_L | Maximum load capacitance (3.3V LVCMOS only). | | | 15 | pF |
| t_{PU} | Power up time for all V_{DDs} to reach minimum specified voltage (power ramps must be monotonic). | 0.05 | | 5 | ms |

Electrical Characteristics

$V_{DDX} = 3.3V \pm 5\%$, $2.5V \pm 5\%$, $1.8V \pm 5\%$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$ unless stated otherwise.

Table 6. Common Electrical Characteristics

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units | Notes |
|-----------------------------|------------|---|-------------------------|---------|-------------------|-------|-------|
| Input Frequency | f_{IN} | Crystal input frequency. | 8 | | 50 | MHz | 1 |
| | | CLKIN input frequency. | 1 | | 240 | MHz | 5 |
| Output Frequency | f_{OUT} | Differential clock output (LVDS/LP-HCSL). | 10 | | 325 | MHz | |
| | | Single-ended clock output (LVCMOS). | 10 | | 200 | MHz | |
| VCO Frequency | f_{VCO} | VCO operating frequency range. | 2400 | 2500 | 2600 | MHz | |
| Loop Bandwidth | f_{BW} | Input frequency = 25MHz. | 0.06 | | 0.9 | MHz | |
| Input High Voltage | V_{IH} | SEL[1:0]. | $0.7 \times V_{DDD}$ | | $V_{DDD} + 0.3$ | V | |
| Input Low Voltage | V_{IL} | SEL[1:0]. | GND - 0.3 | | 0.8 | V | |
| Input High Voltage | V_{IH} | REF/SEL_I2C#. | $0.65 \times V_{DDREF}$ | | $V_{DDREF} + 0.3$ | V | |
| Input Low Voltage | V_{IL} | REF/SEL_I2C#. | -0.3 | | 0.4 | V | |
| Input High Voltage | V_{IH} | XIN/CLKIN. | 0.8 | | 1.2 | V | |
| Input Low Voltage | V_{IL} | XIN/CLKIN. | -0.3 | | 0.4 | V | |
| Input Rise/Fall Time | T_R/T_F | SEL1/SDA, SEL0/SCL. | | | 300 | ns | |
| Input Capacitance | C_{IN} | SEL[1:0]. | | 3 | 7 | pF | |
| Internal Pull-up Resistor | R_{UP} | SEL[1:0] at 25°C. | 200 | 237 | 300 | kΩ | |
| Internal Pull-down Resistor | R_{DOWN} | REF/SEL_I2C#. | 200 | 237 | 300 | kΩ | |

Table 6. Common Electrical Characteristics (Cont.)

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units | Notes |
|--|--------|---|---------|---------|---------|--------|-------|
| Programmable Capacitance at XIN and XO (XIN in parallel with XO) | C_L | XIN/CLKIN, XO. | 0 | | 8 | pF | |
| Input Duty Cycle | t2 | CLKIN, measured at $V_{DDREF}/2$. | 40 | 50 | 60 | % | |
| Output Duty Cycle | t3 | LVC MOS, $f_{OUT} > 156.25\text{MHz}$. | 40 | 50 | 60 | % | |
| | | LVC MOS, $f_{OUT} \leq 156.25\text{MHz}$. | 45 | 50 | 55 | % | |
| | | LVDS, LP-HCSL outputs. | 45 | 50.3 | 55 | % | |
| Clock Jitter | t6 | Cycle-to-cycle jitter (peak-to-peak). See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations. | | 28 | | ps | 4 |
| | | Reference clock RMS phase jitter (12kHz to 5MHz integration range). See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations. | | 338 | | fs rms | 4 |
| | | OUTx RMS phase jitter (12kHz to 20MHz integration range) differential output. See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations. | | 259 | | fs rms | 4 |
| Output Skew | t7 | Skew between the same frequencies, with outputs using the same driver format. | | 105 | | ps | |
| Lock Time | t8 | PLL lock time from power-up. | | 5 | 10 | ms | 2,3 |

¹ Practical lower frequency is determined by loop filter settings.

² Includes loading the configuration bits from OTP to registers.

³ Actual PLL lock time depends on the loop configuration.

⁴ Actual jitter is configuration dependent. These values are representative of what the device can achieve.

⁵ Input doubler off. Maximum input frequency with input doubler on is 160MHz.

Table 7. Test Frequencies for Jitter Measurements in Common Electrical Characteristics Table

| Device | XIN/CLKIN | OUT0 | OUT1 | OUT2 | OUT3 | Unit | Notes |
|----------|-----------|--------|------|------|------|------|-------|
| 9FGV1001 | 50 | 156.25 | | | | MHZ | 1,3 |
| | 50 | 100 | | | | | 2,3 |

¹ This configuration used for 12kHz–20MHz phase jitter measurement.

² This configuration used for PCIe filtered phase jitter measurements.

³ Outputs configured as LP-HCSL or LVDS with REF output off unless noted.

Table 8. LVCMOS Output Electrical Characteristics

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units | Notes |
|-----------------------------------|------------|---|----------------------|---------|-----------|----------|-------|
| Slew Rate | S_R | 3.3V \pm 5%, 20% to 80% of V_{DDO} (output load = 4.7pF). | 2.5 | 3.7 | 4.6 | V/ns | |
| | | 2.5V \pm 5%, 20% to 80% of V_{DDO} (output load = 4.7pF). | 1.5 | 2.4 | 4.6 | | |
| | | 1.8V \pm 5%, 20% to 80% of V_{DDO} (output load = 4.7pF). | 0.8 | 1.7 | 3.5 | | |
| Output High Voltage | V_{OH} | $I_{OH} = -15mA$ at 3.3V. | $0.8 \times V_{DDO}$ | | V_{DDO} | V | |
| | | $I_{OH} = -12mA$ at 2.5V. | | | | | |
| | | $I_{OH} = -8mA$ at 1.8V. | | | | | |
| Output Low Voltage | V_{OL} | $I_{OL} = 15mA$ at 3.3V. | | 0.22 | 0.4 | V | |
| | | $I_{OL} = 12mA$ at 2.5V. | | | | | |
| | | $I_{OL} = 8mA$ at 1.8V. | | | | | |
| Output Leakage Current (OUT[0:1]) | I_{OZDD} | Programmable outputs, tri-state, $V_{DDO} = 3.465V$. | | 0 | 5 | μA | |
| Output Leakage Current (REF) | I_{OZDD} | REF outputs, tri-state, $V_{DDO} = 3.465V$. | | 0 | 5 | μA | |
| CMOS Output Driver Impedance | R_{OUT} | $T_A = 25^\circ C$. | | 17 | | Ω | |

Table 9. LVDS Output Electrical Characteristics

| Parameter | Symbol | Minimum | Typical | Maximum | Units | Notes |
|--|-----------------|---------|---------|---------|-------|-------|
| Differential Output Voltage for the TRUE Binary State | $V_{OT} (+)$ | 247 | 328 | 454 | mV | |
| Differential Output Voltage for the FALSE Binary State | $V_{OT} (-)$ | -454 | -332 | -247 | mV | |
| Change in V_{OT} between Complementary Output States | ΔV_{OT} | | | 50 | mV | |
| Output Common Mode Voltage (Offset Voltage) at 3.3V +5% & 2.5V +5% | V_{OS} | 1.125 | 1.19 | 1.55 | V | |
| Output Common Mode Voltage (Offset Voltage) at 1.8V +5% | V_{OS} | 0.8 | 0.86 | 0.95 | V | |
| Change in V_{OS} between Complementary Output States | ΔV_{OS} | | 0 | 50 | mV | |
| Outputs Short Circuit Current, V_{OUT+} or $V_{OUT-} = 0V$ or V_{DD} | I_{OS} | | 6 | 12 | mA | |
| Differential Outputs Short Circuit Current, $V_{OUT+} = V_{OUT-}$ | I_{OSD} | | 3 | 12 | mA | |
| Rise Times Tested at 20% – 80% | T_R | | 257 | 400 | ps | |
| Fall Times Tested at 80% – 20% | T_F | | 287 | 400 | ps | |

Table 10. Low-Power (LP) Push-Pull HCSL Differential Outputs

 $V_{DD0} = 3.3V \pm 5\%$, $2.5V \pm 5\%$, $1.8V \pm 5\%$, $T_A = -40^\circ C$ to $+85^\circ C$ unless stated otherwise.

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units | Notes |
|--------------------------|--------------------|----------------------|---------|---------|---------|-------|----------|
| Slew Rate | $T_{R/F}$ | Scope averaging on. | 1 | 2.5 | 4 | V/ns | 2,3,16 |
| Slew Rate Matching | $\Delta T_{R/F}$ | | | 9 | 20 | % | 1,14,16 |
| Crossing Voltage (abs) | V_{CROSS} | Scope averaging off. | 250 | 424 | 550 | mV | 1,4,5,16 |
| Crossing Voltage (var) | ΔV_{CROSS} | Scope averaging off. | | 16 | 140 | mV | 1,4,9,16 |
| Voltage High | V_{HIGH} | | 660 | 785 | 850 | mV | 1 |
| Voltage Low | V_{LOW} | | -150 | 13 | 150 | mV | 1 |
| Absolute Maximum Voltage | V_{MAX} | | | 808 | 1150 | mV | 1,7,15 |
| Absolute Minimum Voltage | V_{MIN} | | -300 | -54 | | mV | 1,8,15 |

¹ Measured from single-ended waveform.

² Measured from differential waveform.

³ Measured from -150mV to +150mV on the differential waveform (derived from REFCLK+ minus REFCLK-). The signal must be monotonic through the measurement region for rise and fall time. The 300mV measurement window is centered on the differential zero crossing.

⁴ Measured at crossing point where the instantaneous voltage value of the rising edge of REFCLK+ equals the falling edge of REFCLK-.

⁵ Refers to the total variation from the lowest crossing point to the highest, regardless of which edge is crossing. Refers to all crossing points for this measurement.

⁶ Defines as the absolute minimum or maximum instantaneous period. This includes cycle to cycle jitter, relative ppm tolerance, and spread spectrum modulation.

⁷ Defined as the maximum instantaneous voltage including overshoot.

⁸ Defined as the minimum instantaneous voltage including undershoot.

⁹ Defined as the total variation of all crossing voltages of rising REFCLK+ and falling REFCLK-. This is the maximum allowed variance in V_{CROSS} for any particular system.

¹⁰ Refer to section 4.3.7.1.1 of the PCI Express Base Specification, Revision 3.0 for information regarding ppm considerations.

¹¹ System board compliance measurements must use the test load. REFCLK+ and REFCLK- are to be measured at the load capacitors CL. Single ended probes must be used for measurements requiring single ended measurements. Either single ended probes with math or differential probe can be used for differential measurements. Test load $C_L = 2pF$.

¹² T_{STABLE} is the time the differential clock must maintain a minimum $\pm 150mV$ differential voltage after rising/falling edges before it is allowed to droop back into the $VRB \pm 100mV$ differential range.

¹³ ppm refers to parts per million and is a DC absolute period accuracy specification. 1 ppm is 1/1,000,000th of 100.000000MHz exactly or 100Hz. For 300ppm, then we have an error budget of $100Hz/ppm \times 300 ppm = 30kHz$. The period is to be measured with a frequency counter with measurement window set to 100ms or greater. The $\pm 300 ppm$ applies to systems that do not employ spread spectrum clocking, or that use common clock source. For systems employing spread spectrum clocking, there is an additional 2,500 ppm nominal shift in maximum period resulting from the 0.5% down spread resulting in a maximum average period specification of +2,800 ppm.

¹⁴ Matching applies to rising edge rate for REFCLK+ and falling edge rate for REFCLK-. It is measured using a $\pm 75mV$ window centered on the median cross point where REFCLK+ rising meets REFCLK- falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of REFCLK+ should be compared to the fall edge rate of REFCLK-; the maximum allowed difference should not exceed 20% of the slowest edge rate.

¹⁵ At default amplitude settings.

¹⁶ Guaranteed by design and characterization.

Table 11. Filtered Phase Jitter Parameters – PCIe Common Clocked (CC) Architectures

 T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions; see Test Loads for loading conditions.

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Industry Limits | Units | Notes |
|-------------------|--------------------|---|---------|---------|---------|-----------------|----------|-------|
| PCIe Phase Jitter | $t_{jphPCIeG1-CC}$ | PCIe Gen1. | | 11 | 18 | 86 | ps (p-p) | 1,2,3 |
| | $t_{jphPCIeG2-CC}$ | PCIe Gen2 Low Band 10kHz < f < 1.5MHz (PLL BW of 5–16MHz, 8–16MHz, CDR = 5MHz). | | 0.1 | 0.14 | 3 | ps (rms) | 1,2 |
| | | PCIe Gen2 High Band 1.5MHz < f < Nyquist (50MHz) (PLL BW of 5–16MHz, 8–16MHz, CDR = 5MHz). | | 1.1 | 1.5 | 3.1 | ps (rms) | 1,2 |
| | $t_{jphPCIeG3-CC}$ | PCIe Gen3 (PLL BW of 2–4MHz, 2–5MHz, CDR = 10MHz). | | 0.27 | 0.37 | 1 | ps (rms) | 1,2 |
| | $t_{jphPCIeG4-CC}$ | PCIe Gen4 (PLL BW of 2–4MHz, 2–5MHz, CDR = 10MHz). | | 0.27 | 0.37 | 0.5 | ps (rms) | 1,2 |

Table 12. Filtered Phase Jitter Parameters – PCIe Independent Reference (IR) Architectures

 T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions; see Test Loads for loading conditions.

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Industry Limits | Units | Notes |
|-------------------|----------------------|---|---------|---------|---------|-----------------|----------|-------|
| PCIe Phase Jitter | $t_{jphPCIeG2-SRIS}$ | PCIe Gen2 (PLL BW of 16MHz, CDR = 5MHz). | | 1.1 | 1.34 | 2 | ps (rms) | 1,4,5 |
| | $t_{jphPCIeG3-SRIS}$ | PCIe Gen3 (PLL BW of 2–4MHz, CDR = 10MHz). | | 0.28 | 0.39 | 0.7 | ps (rms) | 1,4,5 |

 Notes for PCIe *Filtered Phase Jitter Parameters* tables:

- ¹ Applies to all differential outputs, guaranteed by design and characterization.
- ² Based on PCIe Base Specification Rev4.0 version 0.7draft. See <http://www.pcisig.com> for latest specifications.
- ³ Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk at 1M cycles for a BER of 1^{-12} .
- ⁴ IR is the new name for Separate Reference Independent Spread (SRIS) and Separate Reference no Spread (SRNS) PCIe clock architectures.
- ⁵ According to the PCIe Base Specification Rev4.0 version 0.7 draft, the jitter transfer functions and corresponding jitter limits are not defined for the IR clock architecture. Widely accepted industry limits using widely accepted industry filters are used to populate this table. There are no accepted filters or limits for IR clock architectures at PCIe Gen1 or Gen4 data rates.

Table 13. Current Consumption

 $V_{DDO} = 3.3V \pm 5\%$, $2.5V \pm 5\%$, $1.8V \pm 5\%$, $T_A = -40^\circ C$ to $+85^\circ C$ unless stated otherwise.

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units | Notes |
|--|--------------|--|---------|---------|---------|-------|-------|
| V_{DDREF} Supply Current | I_{DDREF} | 25MHz REFCLK. | | 4 | 7 | mA | |
| Core Supply Current | I_{DDCORE} | 2500MHz VCO, 25MHz REFCLK. | | 23 | 31 | mA | 3 |
| Output Buffer Supply Current (V_{DDO2}) | I_{DDOx} | LVDS, 325MHz. | | 20 | 26 | mA | 2 |
| | | LP-HCSL, 100MHz. | | 18 | 24 | mA | 2 |
| | | LVC MOS, 50MHz. | | 15 | 20 | mA | 1,2 |
| | | LVC MOS, 200MHz. | | 24 | 39 | mA | 1,2 |
| Output Buffer Supply Current (V_{DDO0} , V_{DDO1} , V_{DDO3} —per output) | I_{DDOx} | LVDS, 325MHz. | | 7 | 11 | mA | 2 |
| | | LP-HCSL, 100MHz. | | 6 | 10 | mA | 2 |
| | | LVC MOS, 50MHz. | | 4 | 7 | mA | 1,2 |
| | | LVC MOS, 200MHz. | | 13 | 25 | mA | 1,2 |
| Total Power Down Current | I_{DDPD} | Programmable outputs in HCSL mode, B37[6,0] = 0. | | 9 | 13 | mA | 2 |
| | | Programmable outputs in LVDS mode, B37[6,0] = 0. | | 24 | 31 | mA | 2 |
| | | Programmable outputs in LVC MOS1 mode, B37[6,0] = 0. | | 4 | 7 | mA | 2 |

¹ Single CMOS driver active for each output pair.

² See Test Loads for details.

³ $I_{DDCORE} = I_{DDA} + I_{DDDIG}$.

I²C Bus Characteristics

 Table 14. I²C Bus DC Characteristics

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|------------------|------------------------|-------------------------|---------|------------------------|-------|
| Input High Level | V _{IH} | — | 0.7 x V _{DDD} | | | V |
| Input Low Level | V _{IL} | — | | | 0.3 x V _{DDD} | V |
| Hysteresis of Inputs | V _{HYS} | — | 0.05 x V _{DDD} | | | V |
| Input Leakage Current | I _{IN} | — | -1 | | 30 | μA |
| Output Low Voltage | V _{OL} | I _{OL} = 3mA. | | | 0.4 | V |

 Table 15. I²C Bus AC Characteristics

| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units |
|--------------------------------------|-----------------------|------------|---------------------------|---------|---------|-------|
| Serial Clock Frequency (SCL) | F _{SCLK} | — | 10 | | 400 | kHz |
| Bus free time between STOP and START | t _{BUF} | — | 1.3 | | | μs |
| Setup Time, START | t _{SU:START} | — | 0.6 | | | μs |
| Hold Time, START | t _{HD:START} | — | 0.6 | | | μs |
| Setup Time, Data Input (SDA) | t _{SU:DATA} | — | 0.1 | | | μs |
| Hold Time, Data Input (SDA) | t _{HD:DATA} | — | 0 | | | μs |
| Output Data Valid from Clock | t _{OVD} | — | | | 0.9 | μs |
| Capacitive Load for Each Bus Line | C _B | — | | | 400 | pF |
| Rise Time, Data and Clock (SDA, SCL) | t _R | — | 20 + 0.1 x C _B | | 300 | ns |
| Fall Time, Data and Clock (SDA, SCL) | t _F | — | 20 + 0.1 x C _B | | 300 | ns |
| High Time, Clock (SCL) | t _{HIGH} | — | 0.6 | | | μs |
| Low Time, Clock (SCL) | t _{LOW} | — | 1.3 | | | μs |
| Setup Time, STOP | t _{SU:STOP} | — | 0.6 | | | μs |

Note: A device must internally provide a hold time of at least 300ns for the SDA signal (referred to the V_{IH(MIN)} of the SCL signal) to bridge the undefined region of the falling edge of SCL.

Crystal Characteristics

Table 16. Recommended Crystal Characteristics

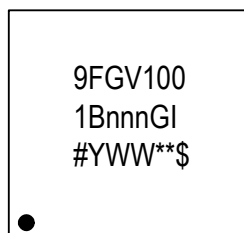
| Parameter | Value | Units |
|---|-------------|-------------|
| Frequency | 8–50 | MHz |
| Resonance Mode | Fundamental | – |
| Frequency Tolerance at 25°C | ±20 | ppm maximum |
| Frequency Stability, REF at 25°C Over Operating Temperature Range | ±20 | ppm maximum |
| Temperature Range (commercial) | 0–70 | °C |
| Temperature Range (industrial) | -40–85 | °C |
| Equivalent Series Resistance (ESR) | 50 | Ω maximum |
| Shunt Capacitance (C_0) | 7 | pF maximum |
| Load Capacitance (C_L) | 8 | pF maximum |
| Drive Level | 0.1 | mW maximum |
| Aging per year | ±5 | ppm maximum |

Package Outline Drawings

The package outline drawings are appended at the end of this document and are accessible from the link below. The package information is the most current data available.

www.idt.com/document/psc/24-vfqfn-package-outline-drawing-40-x-40-x-075-mm-body-05mm-pitch-epad-26-x-26-mm-nbnbg24p2

Marking Diagram



1. Line 1 and 2: truncated part number
2. “#” denotes stepping number.
3. “YWW” denotes the last digits of the year and week the part was assembled.
4. “**” denotes lot number.
5. “\$” denotes mark code.

Ordering Information

| Orderable Part Number | Package | Carrier Type | Temperature |
|-----------------------|---------------------------------|--------------|--------------|
| 9FGV1001BnnnNBGI | 4 × 4 mm, 0.5mm pitch 24-VFQFPN | Tray | -40 to +85°C |
| 9FGV1001BnnnNBGI8 | 4 × 4 mm, 0.5mm pitch 24-VFQFPN | Reel | -40 to +85°C |

“G” indicates RoHS 6.6 compliance.

“nnn” are decimal digits indicating a specific configuration.

Revision History

| Revision Date | Description of Change |
|------------------|---|
| March 28, 2018 | Updated pin 23 descriptions and Output Features on front page. |
| February 6, 2018 | Updated pin 23 descriptions. |
| January 31, 2018 | <ul style="list-style-type: none"> ▪ Updated drive level parameter in <i>Crystal Characteristics</i> table. ▪ Updated <i>Package Outline Drawings</i> text and added hyperlink to document. |
| October 5, 2017 | Initial release. |



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